

Dual ultrafast rugged rectifier diode

Rev. 03 — 18 July 2018

**Product data sheet** 

## 1. Product profile

### **1.1 General description**

Dual ultrafast epitaxial rectifier diodes in a SOT186A (TO-220F) isolated plastic package.

### 1.2 Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance

### **1.3 Applications**

 Output rectifiers in high-frequency switched-mode power supplies

### 1.4 Quick reference data

- Low on-state losses
- Soft recovery minimizes power-consuming oscillations

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	200	V
I <sub>O(AV)</sub>	average output current	SQW; $\delta = 0.5$ ; $T_h \le 92$ °C; both diodes conducting; see Figure 1; see Figure 2	-	-	10	A
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta = 0.5$ ; $t_p = 25 \ \mu s$ ; $T_h \le 92 \ ^\circ C$ ; per diode	-	-	10	A
Dynamic characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery};$ see Figure 5	-	15	25	ns
Static ch	naracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; see <u>Figure 4</u>	-	0.8	0.895	V
Electros	tatic discharge					
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	-	-	8	kV

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode	mb	
3	A2	anode 2		к
mb	n.c.	mounting base; isolated		sym125
			SOT186A	

## 3. Ordering information

### Table 3. Ordering information

Type number	er Package				
	Name	Description	Version		
BYQ28X-200	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

(TO-220F)

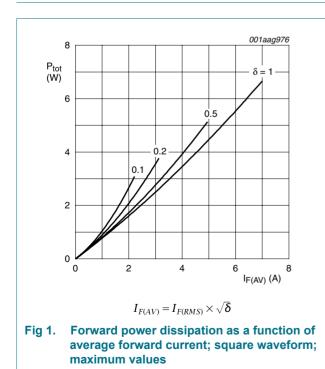
## 4. Limiting values

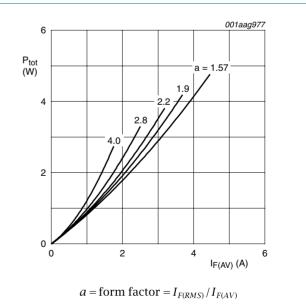
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	200	V
V <sub>RWM</sub>	crest working reverse voltage		-	200	V
V <sub>R</sub>	reverse voltage	DC	-	200	V
I <sub>O(AV)</sub>	average output current	SQW; $\delta = 0.5$ ; T <sub>h</sub> ≤ 92 °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	10	А
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5; $t_p$ = 25 µs; $T_h$ ≤ 92 °C; per diode	-	10	А
I <sub>FSM</sub> non-repetitive peak forward current	· ·	t <sub>p</sub> = 10 ms; SIN; T <sub>j(init)</sub> = 25 °C; per diode	-	50	А
	$t_p = 8.3 \text{ ms; SIN; } T_{j(init)} = 25 \text{ °C; per diode}$	-	55	А	
I <sub>RRM</sub>	repetitive peak reverse current	$t_p = 2 \ \mu s; \ \delta = 0.001$	-	0.2	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.2	А
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Electrosta	tic discharge				
V <sub>ESD</sub>	electrostatic discharge	HBM; C = 250 pF; R = 1.5 k $\Omega$ ; all pins	-	8	kV

 $V_{ESD}$  electrostatic discharge HBM; C = 250 pF; R = 1.5 k $\Omega$ ; all pins voltage

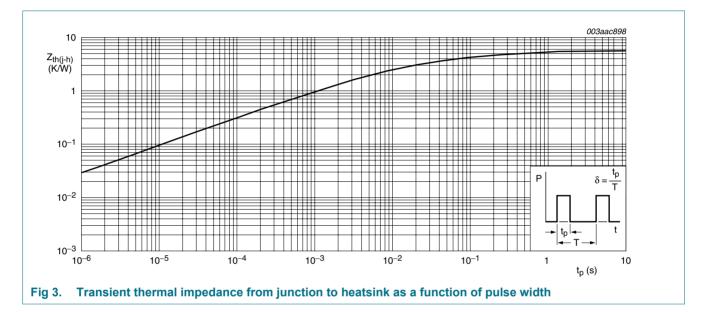






## 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	-	5.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	55	-	K/W

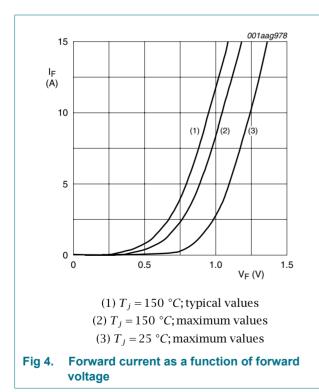


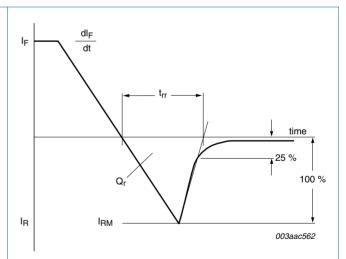
## 6. Isolation characteristics

Table 6.	Isolation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

## 7. Characteristics

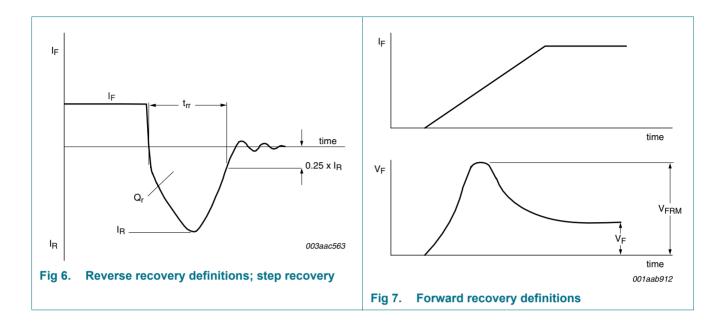
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C	-	1.1	1.25	V
		$I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 4}}{1000 \text{ C}}$	-	0.8	0.895	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C	-	0.95	1.1	V
I <sub>R</sub>	reverse current	$V_R = 200 \text{ V}; \text{ T}_j = 25 \text{ °C}$	-	2	10	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.1	0.2	mA
Dynamic	characteristics					
Qr	recovered charge	I <sub>F</sub> = 2 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 20 A/ $\mu$ s; T <sub>j</sub> = 25 °C	-	4	9	μC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 A$ ; $V_R = 30 V$ ; $dI_F/dt = 100 A/\mu s$ ; ramp recovery; $T_j = 25 \text{ °C}$ ; see Figure 5	-	15	25	ns
		$I_F = 0.5 \text{ A}$ ; $I_R = 1 \text{ A}$ ; step recovery; measured at $I_R = 0.25 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	-	20	ns
I <sub>RM</sub>	peak reverse recovery current	I <sub>F</sub> = 5 A; V <sub>R</sub> ≥ 30 V; dI <sub>F</sub> /dt = 50 A/µs; T <sub>j</sub> = 25 °C; see <u>Figure 5</u>	-	0.5	0.7	А
V <sub>FRM</sub>	peak forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 10 A/µs; T <sub>j</sub> = 25 °C; see <u>Figure 7</u>	-	1	-	V



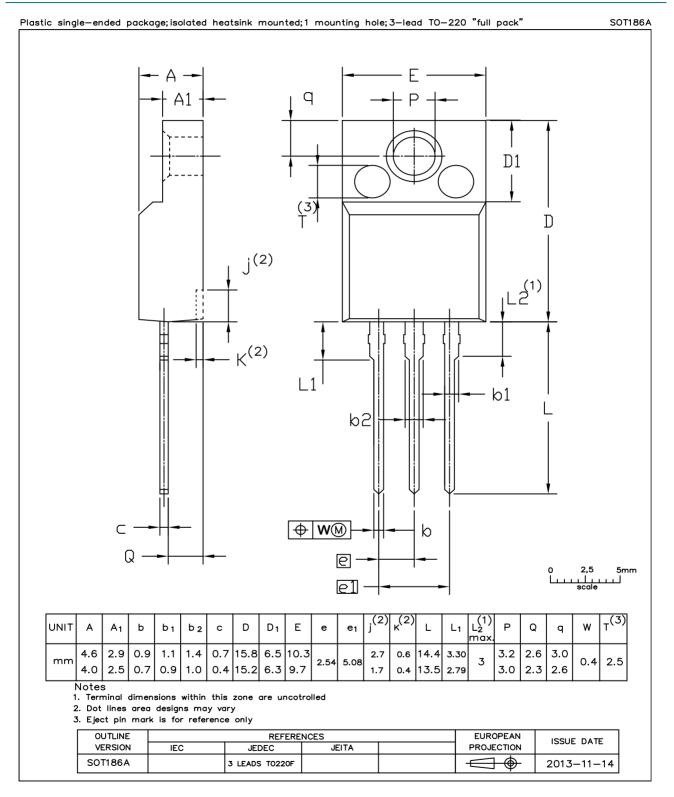




### Dual ultrafast rugged rectifier diode



### 8. Package outline



#### Fig. 8. Package outline TO-220F (SOT186A)

BYQ28X-200\_3

## 9. Revision history

## Table 8. Revision history

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Document ID	Release date	Data sheet status	Change notice	Supersedes
BYQ28X-200_3	20180718	Product data sheet	-	BYQ28X-200_2
Modifications:	<ul> <li>Change N</li> </ul>	XP logo to WeEn logo.		
	<ul> <li>Update PC</li> </ul>	D to combine different as	ssembly plant.	
BYQ28X-200_2	20090205	Product data sheet	-	BYQ28X_SERIES_1
Modifications:		t of this data sheet has be of NXP Semiconductors.	een redesigned to comp	ly with the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to th	e new company name v	where appropriate.
	<ul> <li>Type number</li> </ul>	per BYQ28X-200 separate	ed from data sheet BYQ	28X_SERIES_1.
BYQ28X_SERIES_1	19960801	Product data sheet	-	-

#### Dual ultrafast power diode

## 10. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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